FLAG-ERA 2022 Project Workshop

March 21th 2022

Transferable two-dimensional correlated oxide layers



FLAG-ERA JTC 2019. **Euro Flag ERA Call 2019** FlagERA ERA-NET Cofund Horizon 2020 Programme (1/1/2020- 31/1/2023)

1/4/2020 through 31/3/2023

extended through 31/12/2023



FLAG-ERA JTC 2019 Full Proposal



Project Acronym

To2Dox

Project Full Title

Transferable two-dimensional correlated oxide layers

Sub-call: Graphene – Basic Research	с
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Graphene – Applied research and innovation

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HBP – Basic and applied research

Main area within sub-call (1, 2, 3...)

Secondary area(s) (If several, separate with commas)

Duration 36 months

Partners and participants involved in the realisation of the project

Partner Number	Country	Institution/ Department	Name of the Principal Investigator (PI) ²	Name of the co- Investigators ³	Other participants ⁴		
1 Coordinator	Spain	Univ. Complutense / Dpt. Materials Physics	Jacobo Santamaria	Carlos Leon	Alberto Rivera- Calzada. Maria Varela , 1 post doc		
2	Spain	CSIC/ Inst. Ciencia de Materiales Madrid	Mar Garcia- Hernandez	Andres Castellanos- Gomez	1 postdoc		
3	France	CNRS THALES/ Unite Mixte de Physique	Javier Villegas	Karim Bouzehouane	Anke Sander; Javier Briatico, 1 postdoc		
4	Germany	Max Planck Institute fuer Festkoerper Forschung	Jochen Mannhart	NN	1 PhD student		
5	Germany	Forschungszentrum Jülich/PGI-7	Regina Dittmann	Felix Gunkel	1 PhD student		
6	Latvia	University of Latvia/ Inst. Solid State Physics	Sergei Piskunov	Eugene Kotomin	Yuri Mastrikov, 1 postdoc		

Transferable two-dimensional correlated oxide layers To2Dox







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GANNT	T CHART		YEAR 1			YEAR 2			YEAR 3		M1	20	WP1,	Fabrication of a new family of freestanding 2D
WPs	TASKs	M/ 1-4	5-8	9-12	13-16	17-20	21-24	25-28	29-32	33-36			WP2,	correlated oxides
WP1	T1.1				D1.1								WP3	
	T1.2				D1.1						M2	28	WP2,	Understanding the role of defects on the stability and
	T1.3					D1.2							WP3,	properties of 2D oxides
WP2	T2.1					D2.1			D2.2				WP4	
	T2.2					D2.1			D2.2		M3	34	WP1,	Identification of proximity effects at interfaces
	T2.3					D2.1			D2.2				WP2,	between 2D oxides and 2D VdW materials
	т2.4					D2.1			D2.2				WP3,	
14/50	T 0.4						D 0.0		D2.3				WP4	
WP3	13.1 T2.2						D3.2							
	T3.2						D2.1		D3 3			WPA		WP1 Fabrication of 2D oxides
	T4.4								D3.3					
VVP4	T4.1								04.1	D4 2		K WP2		WP2 Defect characterization
	T4.3									D4.2	/ 🔸		>	of 2D oxides
WP5	T5.1	D5.1												
**** 0		D5.4									-	WP 1		WP3 Functional characterization
	T5.2					D5.5				D5.6			M	of 2D oxides
	T5.3	D5.2											*	of 2D oxides
		D5.3										WP3		WD4 Developite interactions
							Mile1	Mile2	M	ile3▲				WP4 Proximity interactions:
														2D oxides/V.d.W. layers
												WPS	5	WP5 Management
erable	Month of	Title of	deliverabl	е										
	delivery									D3.1	22	Af	reestanding	ferroelectric BaTiO ₃ layer
	14	Unit ce	Il thick oxi	de layers v	with optim	nized prop	erties			D3.2	24	Fre	estanding fe	erromagnetic La _{0.7} Sr _{0.2} MnO ₂ and SrRuO ₂ layers

D3.3

30

D2.1	18	First report on structure and chemistry of defects in freestanding 2D oxides. Partial (preliminary) report will be delivered in month 12.
D2.2	32	Final report on defects structures of 2D oxides and their manipulation. Partial (preliminary)report will be delivered in month 24
D2.3	32	Final report on theoretical simulations of defects structures of 2D

oxides. Preliminary reports will be delivered in months 12 and 24

Freestanding layers of correlated 2D oxides

D1.2

20

D4.1	32	Report on field effect modification of VdW layers with freestanding ferroelectrics
D4.2	34	Report on spin textures induced in 2D oxide ferromagnets by spin orbit proximity effect
D4.3	36	Report on superconducting proximity effect between a d wave superconductor and a topological insulator.

A freestanding YBa₂Cu₃O₇ superconductor

WP1. Fabrication and manipulation of freestanding layers of correlated TMOs.

HAADF-STEM -SrTiO3 SrRuO₃ -SrTiO₃ Figure 1. STEM cross-sectional cut through a unit-cell thick SrRuO₃ layer embedded in SrTiO₃. The sample has been grown by PLD. (1)(2) 3 PDMS stamp PDMS stamp PDMS stamp

Freestanding correlated oxides are a new family of materials

with potentially interesting collective groundstates stable at room temperature

PDMS stamp

PDMS star sto acceptor substrate



BaTiO₃



Deterministic BTO placement

Our procedure allows transferring the fabricated bilayers to different target substrates, including **TEM grids** for structural characterization.

D1.2 Freestanding layers of correlated 2D oxides

WP1. Fabrication and manipulation of freestanding layers of correlated TMOs.

Colour charts for BTO samples \rightarrow optical thickness identification for different substrates



D1.1 Unit cell thick epitaxial oxide layers D1.2 Freestanding layers of correlated 2D oxides

S. Puebla, et al (in preparation)



$$E_f = 3\left(\frac{\lambda}{2\pi h}\right)^3 \frac{1-\nu_f^2}{1-\nu_s^2} E_s$$

 $E_{f/s}$ – Young's modulus film/substrate $v_{f/s}$ – Poisson ratio film/substrate λ – Ripples periodicity h – Film thickness S. Puebla, V. I

Measured Young's modulus BTO flakes : 13±1 GPa

**Young's modulus BTO_{bulk} : ~67 GPa

Ref: IEEE 5th International Symposium on Micro Machine and Human Science proceedings 1994, p.75

S. Puebla, V. Rouco et al .. A. Castellanos (in preparation) D3.1 A freestanding ferroelectric BaTiO3 layer

Sucessful exfoliation and transfer of SrTiO₃ lamellae

 Al_2O_3



⁽ XRD and XPS analysis confirm the transfer of a crystalline SrTiO₃ layer

D3.1 A freestanding SrTiO3 layer

Remote epitaxy of SrTiO₃ on graphene

laser aperture



intensity is lowest for the smallest \checkmark High quality SrTiO₃ is grown on graphene

✓ Damage of graphene (D-band) can be minimised by plume confinement

WP. 2. Study of the defect chemistry and structure of freestanding 2D oxide layers.



NCM



- We transfer a freestanding BTO flake into a porous SiN membrane. Flakes have 10s of microns size.
- Atomic resolution Z-contrast STEM images show some small defect structures at the surface of the transferred flake.
- The edge of the flake is atomically sharp

At the white spots the transition probability of the $2p_{3/2} \rightarrow e_g$ transition, and to less extent that of $2_{p3/2} \rightarrow t_{2g}$, are diminished compared with those at the rest of the crystal.

Release of strain is expected to produce a new defect zoology which is interesting to examine both experimentally and theoretically





nm

Bulk

- We find 1D defects at the flake with extra Ti atoms -
- EELS analysis at the 1D defect shows a Ti reduction to 3.8 oxidation state -

Discrete defect model for free standing oxides



First principles simulations of defect structures at TiO₂ (110) surface: Predictions from RT-TDDFT calculations



Real-time -dependent density functional theory (RT-TDDFT) calculations are performed to analyze the optical property and charge transitions on the rutile TiO_2 (110) surface.

- L. L. Rusevich, M.Tyunina, E.A. Kotomin N. Nepomniashchaia & A. Dejne Sci. Rep. (2021) 11:23341
- RI Eglitis, EA Kotomin, Al Popov, SP Kruchinin, R Jia J Low Temperature Physics 48 (1), 80-88 (2022)
- Maksim Sokolov et al. Catalysts 2021, 11, 1326.

D2.1 First report on structure and chemistry of defects in freestanding 2D oxides.

WP 3. Characterization of new electronic groundstates in freestanding 2D oxides.

Functional response of freestanding oxides may vary compared to the "substrate –supported" counterparts. Are correlated states stable in freestanding form?

Polarization on single film





Single films show homogeneous in-plane polarization



Ti displacement from center Ba sublattice

Mean (Px) = 0.16 Å Mean (Py) = 0.10 Å



WP 3. Characterization of new electronic groundstates in freestanding 2D oxides.

Functional response of freestanding oxides may vary compared to the "substrate –supported" counterparts. Are correlated states stable in freestanding form?

Piezoelectric Force Microscopy→ Switching of ferroelectric domains



rieestanunig DIO/GOIU substiate

D3.1 A freestanding ferroelectric BaTiO3 layer

WP 3. Characterization of new electronic groundstates in freestanding 2D oxides.

Functional response of freestanding oxides may vary compared to the "substrate –supported" counterparts. Are correlated states stable in freestanding form?



- R. El Hage ...J. Santamaria J. E Villegas Nature Electronics (under consideration)
- D. Sanchez-Manzano ... J. E Villegas and J. Santamaria Nature Materials 21, 188 (2022)
- Myoung Y Woo, J. Santamaria and J. E. Villegas Nature Comms. 12:3283 (2021)

D3.3 A freestanding YBCO BSSCO superconductor

WP 4. Exploratory study of proximity interactions at interfaces between 2D correlated oxides and 2D van der Waals materials Exciting new proximity phenomena with vdW materials can be anticipated.

Device fabrication \rightarrow FET configuration using BTO flake as gate dielectric

MoS₂ Au Au BTO SiO₂ 10 × 10⁻⁷ (40nm) hBN 9 BTO 8 x50 I_{SD}/width (A/µm) BTO 3 6 µm 2 MoS $V_{SD}=1V$ 5.5 µm -40 -30 -20 -10 0 10 20 30 40 50 -50 V_G (V) μ_{BTO} = 15 cm²V⁻¹s⁻¹ $\mu_{hBN} = 0.8 \text{ cm}^2 \text{V}^{-1} \text{s}^{-1}$

Partner 2 CSIC

S. Puebla, V. Rouco et al.... A. Castellanos (in preparation)

D4.1 Report on FE modification of VdW layers with freestanding BTO

Device fabrication \rightarrow Field effect control of MoS₂ optical emission



PL spectra of MoS₂ modified by BTO gating



D4.1 Report on **F**E modification of VdW layers with freestanding BTO

Management. RRI.

WP 5	Project management, dissemination and exploitation of results and	Start	End
	Communication with the Graphene Flagship. Leader: Mar Garcia-	month	month
	Hernandez (ICMM-CSIC).	1	36

Deliverable	Month of delivery	Title of deliverable
D5.1	2	Project's website.
D5.2	3	Data Management Plan (DMP).
D5.3	4	Project's database.
D5.4	4	Dissemination and Exploitation of the results plan (DERP).
D5.5	19	Intermediate Report.
D5.6	36	Final Report.

- We have asked and obtained a cost-ineffective a **project extension** until December 2023
- **Gender** balance (2 node leaders are female researchers)
- The Project management Board PMB (formed by the PI of the different nodes of the consortium) has delivered a <u>Data Management Plan</u>,
- The Dissemination and Communication Board DCB has elaborated a <u>Publication protocol</u>; With a data tracking system
- A project Webpage has been delivered

https://gfmc.fis.ucm.es/to2dox/



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To2Dox

Progress Meeting held (1/03/2022)

1/4/2020 through 31/3/2023

GANNT	CHART		YEAR 1			YEAR 2		YEAR 3			
WPs	TASKs	M/ 1-4	5-8	9-12	13-16	17-20	21-24	25-28	29-32	33-36	
WP1	T1.1				D1.1						
	T1.2				D1.1						
	T1.3					D1.2					
WP2	T2.1					D2.1			D2.2		
	T2.2					D2.1			D2.2		
	T2.3					D2.1			D2.2		
	T2.4					D2.1			D2.2		
									D2.3		
WP3	T3.1						D3.2				
	T3.2						D3.1				
	T3.3								D3.3		
WP4	T4.1								D4.1		
	T4.2									D4.2	
	T4.3									D4.3	
WP5	T5.1	D5.1									
		D5.4									
	T5.2					D5.5				D5.6	
	T5.3	D5.2									
		D5.3									

- L. L. Rusevich, M.Tyunina, E.A. Kotomin N. Nepomniashchaia & A. Dejne The electronic properties of SrTiO3-δ with oxygen vacancies or substitutions Sci. Rep. (2021) 11:23341
- RI Eglitis, EA Kotomin, AI Popov, SP Kruchinin, R Jia Comparative ab initio calculations of SrTiO3, BaTiO3, PbTiO3, and SrZrO3 (001) and (111) surfaces as well as oxygen vacancies J Low Temperature Physics 48 (1), 80-88 (2022)
- Extremely long-range, high-temperature Josephson coupling across a half-metallic ferromagnet D. Sanchez-Manzano ... J. E Villegas and J. Santamaria Nature Materials 21, 188 (2022)

Relation with Graphene Flagship. Work package 3 (To2Dox is Ass. Member of the Graphene Flagship)



 Methodology for <u>Assembling</u> <u>heterostructures</u> combining freestanding layers





CONCLUSIONS:

- We have delivered fabrication protocols of **freestanding BTO and STO** layers on arbitrary substrates.
- We have characterized the mechanical and ferroelectric properties of the BTO free standing layers.
- We have characterized the superconducting properties and the effect of illumination of BSCCO freestanding layers.
- We have produced the first heterostructures BTO/ 2D VdW materials in FET devices and have started to explore
 systematically their transport and optical properties. There is path for improvement by making devices in vacuum
 and improve the interfaces

NEXT STEPS

- PLD growth of water solvable buffer layers
- Superconductor devices
- Magnetic freestanding layers. Proximity to superconductors
- Defect characterization